DG271B

## High-Speed Quad Monolithic SPST CMOS Analog Switch

## FEATURES

- Fast Switching ton: 55 ns
- Low Charge Injection: 5 pC
- Low rids(on): $32 \Omega$
- TTL/CMOS Compatible
- Low Leakage: 50 pA

BENEFITS

- Fast Settling Times
- Reduced Switching Glitches
- High Precision
APPLICATIONS
- High-Speed Switching
- Sample/Hold
- Digital Filters
- Op Amp Gain Switching
- Flight Control Systems
- Automatic Test Equipment
- Choppers
- Communication Systems


## DESCRIPTION

The DG271B high speed quad single-pole single-throw analog switch is intended for applications that require low on-resistance, low leakage currents, and fast switching speeds.

Built on the Vishay Siliconix' proprietary high voltage silicon gate process to achieve superior on/off performance, each switch conducts equally well in both directions when on, and blocks up to the supply voltage when off. An epitaxial layer prevents latchup.

The DG271B has a redesign internal regulator which improves start-up over the DG271.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead $(\mathrm{Pb})$-free device terminations. For analog switching products manufactured with $100 \%$ matte tin device terminations, the lead (Pb)-free "-E3" suffix is being used as a designator.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION


| TRUTH TABLE |  |
| :---: | :---: |
| Logic | Switch |
| 0 | ON |
| 1 | OFF |

Logic " 0 " $\leq 0.8 \mathrm{~V}$
Logic " 1 " $\geq 2.4 \mathrm{~V}$

| ORDERING INFORMATION |  |  |
| :---: | :---: | :--- |
| Temp Range | Package | Part Number |
| 0 to $70^{\circ} \mathrm{C}$ | 16-Pin Plastic DIP | DG271BCJ-E3 |
| -40 to $85^{\circ} \mathrm{C}$ | 16-Pin Narrow SoIC | DG271BDY-E3 |
|  |  | DG271BDY-T1-E3 (with Tape and Reel) |

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## ABSOLUTE MAXIMUM RATINGS

| $\mathrm{V}+$ to V - |  |  |
| :---: | :---: | :---: |
| GND to V- . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . 25 V |  |  |
| Digital Inputs ${ }^{\text {a }} \mathrm{V}_{\mathrm{S}}, \mathrm{V}_{\mathrm{D}}$ |  | $\ldots$. (V-) -2 V to ( $\mathrm{V}+$ ) +2 V or 20 mA , whichever occurs first |
| Current, Any Terminal |  | 30 mA |
| Peak Current, S or D |  |  |
| (Pulsed at $1 \mathrm{~ms}, 10 \%$ duty cycle max) |  | 100 mA |
| Storage Temperature | (DY Suffix) | -65 to $150^{\circ} \mathrm{C}$ |
|  | (CJ Suffix) | .... -65 to $125^{\circ} \mathrm{C}$ |

Power Dissipation (Package)b
16-Pin Plastic DIPc
470 mW
16-Pin Plastic Narrow SOICd
600 mW

## Notes:

a. Signals on $S_{X}, D_{X}$, or $I_{X}$ exceeding $V+$ or $V$ - will be clamped by internal diodes. Limit forward diode current to maximum current ratings
b. All leads welded or soldered to PC Board.
c. Derate $6.5 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $75^{\circ} \mathrm{C}$
d. Derate $7.6 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $75^{\circ} \mathrm{C}$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

| SPECIFICATIONS ${ }^{\text {a }}$ |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Parameter | Symbol | Test Conditions Unless Specified$\begin{gathered} \mathrm{V}_{+}=15 \mathrm{~V}, \mathrm{~V}-=-15 \mathrm{~V} \\ \mathrm{~V}_{\text {IN }}=2.4 \mathrm{~V}, 0.8 \mathrm{~V}^{f} \end{gathered}$ | Temp ${ }^{\text {b }}$ | $\begin{gathered} \text { C, D Suffix } \\ 0 \text { to } 70^{\circ} \mathrm{C} \\ -40 \text { to } 85^{\circ} \mathrm{C} \end{gathered}$ |  |  | Unit |
|  |  |  |  | Min ${ }^{\text {d }}$ | Typ ${ }^{\text {c }}$ | Max ${ }^{\text {d }}$ |  |
| Analog Switch |  |  |  |  |  |  |  |
| Analog Signal Range ${ }^{\text {e }}$ | $V_{\text {ANALOG }}$ |  | Full | -15 |  | 15 | V |
| Drain-Source On-Resistance | $\mathrm{r}_{\mathrm{DS}}(\mathrm{on})$ | $\mathrm{I}_{\mathrm{S}}=1 \mathrm{~mA}, \mathrm{~V}_{\mathrm{D}}= \pm 10 \mathrm{~V}$ | Room Full |  | 32 | $\begin{aligned} & 50 \\ & 75 \end{aligned}$ | $\Omega$ |
| Switch Off Leakage Current | $I_{\text {S(off) }}$ | $\mathrm{V}_{\mathrm{D}}= \pm 14 \mathrm{~V}, \mathrm{~V}_{S}=\mp 14 \mathrm{~V}$ | $\begin{gathered} \hline \text { Room } \\ \text { Full } \end{gathered}$ | $\begin{gathered} \hline-1 \\ -20 \end{gathered}$ | $\pm 0.05$ | $\begin{gathered} 1 \\ 20 \end{gathered}$ | $n A$ |
|  | ${ }_{\mathrm{L}}^{\mathrm{offi}}$ ) |  | $\begin{gathered} \hline \text { Room } \\ \text { Full } \end{gathered}$ | $\begin{gathered} \hline-1 \\ -20 \end{gathered}$ | $\pm 0.05$ | $\begin{gathered} \hline 1 \\ 20 \end{gathered}$ |  |
| Channel On Leakage Current | $\begin{gathered} \mathrm{I}_{\mathrm{D}(\mathrm{on})}+ \\ \mathrm{I}_{\mathrm{S}(\text { on }}+ \end{gathered}$ | $\mathrm{V}_{\mathrm{S}}=\mathrm{V}_{\mathrm{D}}= \pm 14 \mathrm{~V}$ | $\begin{gathered} \hline \text { Room } \\ \text { Full } \end{gathered}$ | $\begin{gathered} \hline-1 \\ -20 \end{gathered}$ | $\pm 0.05$ | $\begin{gathered} 1 \\ 20 \end{gathered}$ |  |
| Digital Control |  |  |  |  |  |  |  |
| Input Current with Voltage High | $\mathrm{I}_{\text {INH }}$ | $\mathrm{V}_{\text {IN }}=2 \mathrm{~V}$ | Full | -1 | 0.010 | 1 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\text {IN }}=15 \mathrm{~V}$ | Full | -1 | 0.010 | 1 |  |
| Input Current with Voltage Low | $\mathrm{I}_{\text {INL }}$ | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ | Full | -1 | 0.010 | 1 |  |
| Dynamic Characteristics |  |  |  |  |  |  |  |
| Turn-On Time | ton | $V_{S}= \pm 10 \mathrm{~V}$ <br> See Figure 3 | Room Full |  | 55 | $\begin{aligned} & 65 \\ & 80 \end{aligned}$ | ns |
| Turn-Off Time | toff |  | $\begin{gathered} \hline \text { Room } \\ \text { Full } \end{gathered}$ |  | 50 | $\begin{aligned} & 65 \\ & 80 \end{aligned}$ |  |
| Charge Injection | Q | $\begin{gathered} \mathrm{C}_{\mathrm{L}}=1 \mathrm{nF}, \mathrm{~V}_{\mathrm{S}}=0 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{gen}}=0 \mathrm{~V}, \mathrm{R}_{\text {gen }}=0 \Omega \\ \text { See Figure } 3 \end{gathered}$ | Room |  | -5 |  | pC |
| Source Off Capacitance | $\mathrm{C}_{\text {S(off) }}$ | $\begin{gathered} V_{S}=0 V, V_{i N}=5 V \\ f=1 \mathrm{MHz} \end{gathered}$ | Room |  | 8 |  | pF |
| Drain Off Capacitance | $\mathrm{C}_{\mathrm{D} \text { (off) }}$ |  | Room |  | 8 |  |  |
| Channel On Capacitance | $\mathrm{C}_{\mathrm{D} \text { (on) }}$ | $\mathrm{V}_{\mathrm{D}}=\mathrm{V}_{\mathrm{S}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ | Room |  | 30 |  |  |
| Off Isolation | OIRR | $\begin{aligned} & C_{L}= 10 \mathrm{pF}, R_{\mathrm{L}}=1 \mathrm{k} \Omega \\ & \mathrm{f}=100 \mathrm{kHz} \end{aligned}$ <br> See Figures 4 and 5 | Room |  | 85 |  | dB |
| Crosstalk | $\mathrm{X}_{\text {TALK }}$ |  | Room |  | 100 |  |  |
| Supply |  |  |  |  |  |  |  |
| Positive Supply Current | $1+$ | All Channels On or Off $\mathrm{V}_{\mathrm{IN}}=5 \mathrm{~V}$ or 0 V | Room Full |  | 5.5 | $\begin{gathered} 7.5 \\ 9 \end{gathered}$ | mA |
| Negative Supply Current | I- |  | $\begin{gathered} \hline \text { Room } \\ \text { Full } \end{gathered}$ | $\begin{aligned} & \hline-6 \\ & -8 \end{aligned}$ | -3.4 |  |  |

## Notes:

a. Refer to PROCESS OPTION FLOWCHART.
b. Room $=25^{\circ} \mathrm{C}$, Full $=$ as determined by the operating temperature suffix.
c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet
e. Guaranteed by design, not subject to production test.
f. $\quad \mathrm{V}_{\mathrm{IN}}=$ input voltage to perform proper function.

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TYPICAL CHARACTERISTICS ( $25^{\circ} \mathrm{C}$ UNLESS NOTED)








FIGURE 1.

## TEST CIRCUITS



FIGURE 2. Switching Time

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